

2SC4533

Silicon NPN triple diffusion planar type

For high breakdown voltage high-speed switching

■ Features

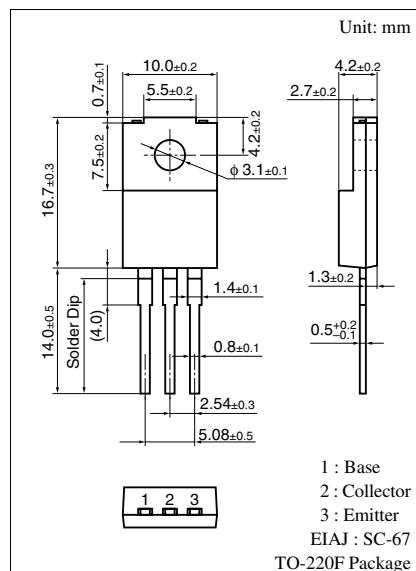
- High-speed switching
- High collector to base voltage V_{CBO}
- Wide area of safe operation (ASO)
- Satisfactory linearity of forward current transfer ratio h_{FE}
- Full-pack package which can be installed to the heat sink with one screw

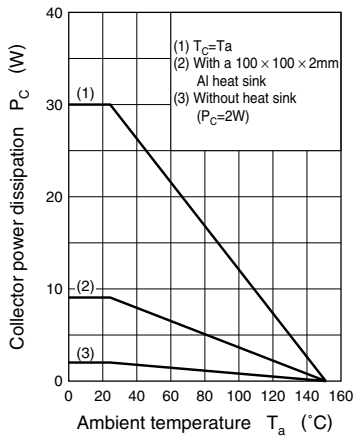
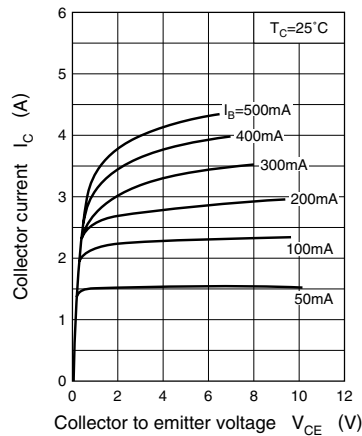
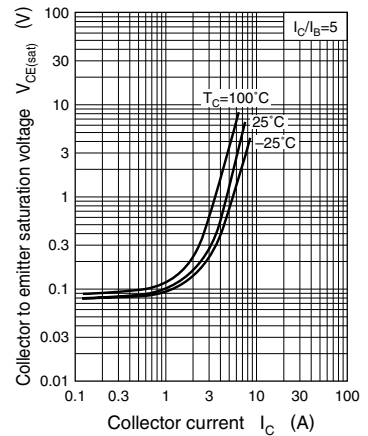
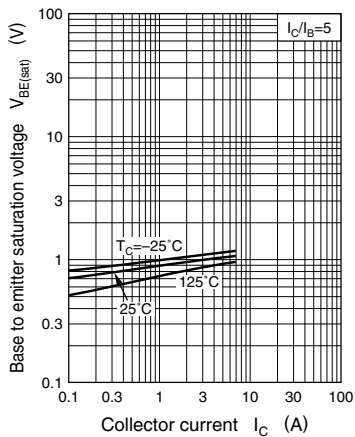
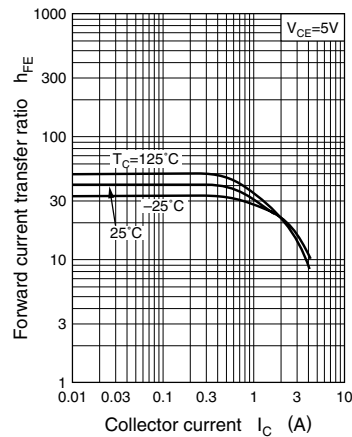
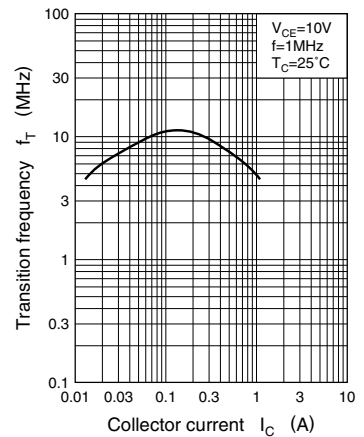
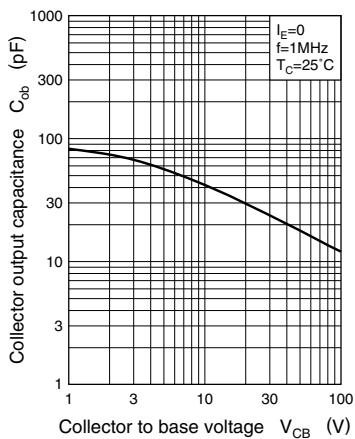
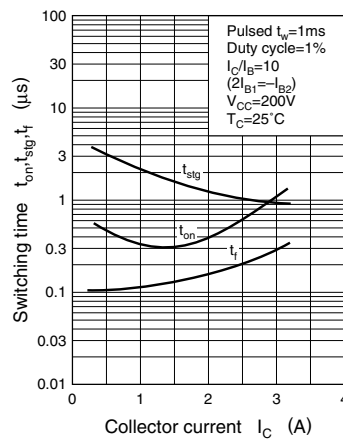
■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter		Symbol	Rating	Unit
Collector to base voltage		V_{CBO}	500	V
Collector to emitter voltage		V_{CES}	500	V
		V_{CEO}	400	V
Emitter to base voltage		V_{EBO}	7	V
Peak collector current		I_{CP}	6	A
Collector current		I_C	3	A
Base current		I_B	1.2	A
Collector power dissipation	$T_C = 25^{\circ}\text{C}$	P_C	30	W
	$T_a = 25^{\circ}\text{C}$		2	
Junction temperature		T_j	150	$^{\circ}\text{C}$
Storage temperature		T_{stg}	-55 to +150	$^{\circ}\text{C}$

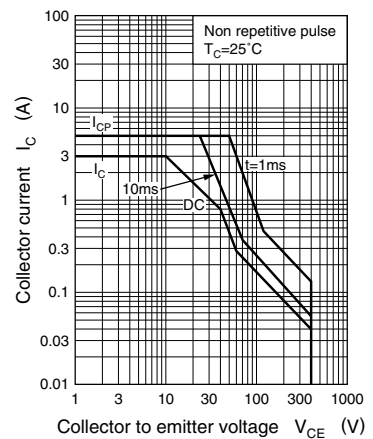
■ Electrical Characteristics $T_C = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 500\text{ V}, I_E = 0$			100	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 5\text{ V}, I_C = 0$			100	μA
Collector to emitter voltage	V_{CEO}	$I_C = 10\text{ mA}, I_B = 0$	400			V
Forward current transfer ratio	h_{FE1}	$V_{CE} = 5\text{ V}, I_C = 0.1\text{ A}$	10			
	h_{FE2}	$V_{CE} = 2\text{ V}, I_C = 1.2\text{ A}$	8		40	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 1.5\text{ A}, I_B = 0.3\text{ A}$			1.0	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = 1.5\text{ A}, I_B = 0.3\text{ A}$			1.5	V
Transition frequency	f_T	$V_{CE} = 10\text{ V}, I_C = 0.2\text{ A}, f = 1\text{ MHz}$		10		MHz
Turn-on time	t_{on}	$I_C = 1.5\text{ A}, I_{B1} = 0.15\text{ A}, I_{B2} = -0.3\text{ A}, V_{CC} = 200\text{ V}$			1.0	μs
Storage time	t_{stg}				3.0	μs
Fall time	t_f				0.3	μs

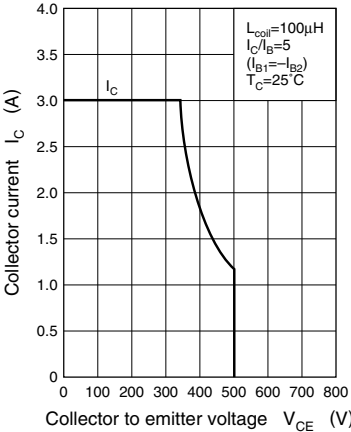


$P_C - T_a$  $I_C - V_{CE}$  $V_{CE(sat)} - I_C$  $V_{BE(sat)} - I_C$  $h_{FE} - I_C$  $f_T - I_C$  $C_{ob} - V_{CB}$  $t_{on}, t_{stg}, t_f - I_C$ 

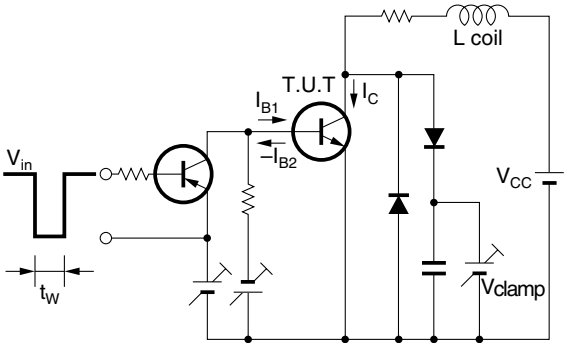
Area of safe operation (ASO)



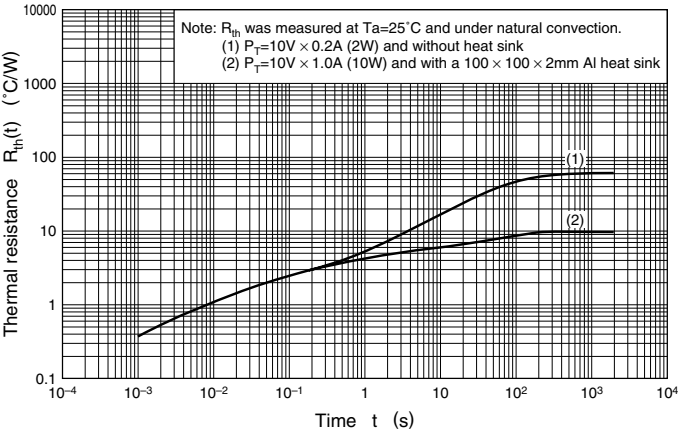
Area of safe operation, reverse bias ASO



Reverse bias ASO measuring circuit



$R_{th(t)} - t$



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